

PLUS Search Results for S/N 09/774,888, Searched April 26, 2002 (top 50)

5385854	6106734	5541871	5413948	5208172
6005270	6137120	5599727	5526304	5235189
6335716	6177706	5731232	5734179	5250835
5904526	6225668	5352916	5904512	5252849
5702988	6225668	5460995	5982004	5266507
5738731	6232173	5821564	6049106	5275964
5847411	6300664	6022770	6211076	5278459
5880991	6320782	5324960	6211076	5281843
6025252	5471071	5379251	4980732	5308782
6039857	5295107	5404326	5198683	

**Most Frequently Occurring Classifications of Patents Returned  
From A Search of 09/774,888 on April 26, 2002**

**Combined Classifications**

14 257/903

7 257/66

6 257/316

6 257/369

5 257/347

5 257/67

5 365/154

4 257/315

4 257/368

4 257/393

4 257/69

3 257/329

3 257/350

3 257/351

3 438/154

3 438/158

2 136/249

2 136/260

2 136/262

2 257/296

2 257/298

2 257/300

2 257/306

2 257/310

2 257/311

2 257/317

2 257/319

2 257/390

2 257/401

2 257/64

2 365/145

2 365/156

2 438/153

2 438/156

2 438/211

2 438/253

2 438/257

2 438/665

2 438/666

- 14 257/903 (0 OR, 14 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/903 FET CONFIGURATION ADAPTED FOR USE AS STATIC  
MEMORY CELL
- 7 257/66 (2 OR, 5 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/55 ...Amorphous semiconductor is alloy or contains  
material to change band gap (e.g., Si Ge , SiN )  
257/66 .Field effect device in non-single crystal, or  
recrystallized, semiconductor material
- 6 257/316 (0 OR, 6 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS  
diode)  
257/314 ..Variable threshold (e.g., floating gate  
memory device)  
257/315 ...With floating gate electrode  
257/316 ....With additional contacted control electrode
- 6 257/369 (1 OR, 5 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS  
diode)  
257/368 ..Insulated gate field effect transistor in  
integrated circuit  
257/369 ...Complementary insulated gate field effect  
transistors
- 5 257/347 (2 OR, 3 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/213 FIELD EFFECT DEVICE  
257/288 .Having insulated electrode (e.g., MOSFET, MOS  
diode)  
→ 257/347 ..Single crystal semiconductor layer on  
insulating substrate (SOI)
- 5 257/67 (3 OR, 2 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/55 ...Amorphous semiconductor is alloy or contains  
material to change band gap (e.g., Si Ge , SiN )  
257/66 .Field effect device in non-single crystal, or  
recrystallized, semiconductor material  
257/67 ..In combination with device formed in single  
crystal semiconductor material (e.g., stacked FETs)
- 5 365/154 (1 OR, 4 XR)  
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL  
365/129 SYSTEMS USING PARTICULAR ELEMENT  
365/154 .Flip-flop (electrical)